

ABSTRACT OF THE DISCLOSURE

In using an epitaxial growth method to selectively grow on a silicon substrate an epitaxial layer on which an element is to be formed, the epitaxial layer is
5 formed so as to extend upward above a thermal oxide film that is an element isolating insulating film, in order to prevent formation of facets. Subsequently, unwanted portions of the epitaxial layer are removed by means of CMP to complete an STI element isolating
10 structure.